Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	1152
Number of Logic Elements/Cells	11520
Total RAM Bits	147456
Number of I/O	408
Number of Gates	728000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	652-BGA
Supplier Device Package	652-BGA (45x45)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=ep20k300ebc652-1

Cascade Chain

With the cascade chain, the APEX 20K architecture can implement functions with a very wide fan-in. Adjacent LUTs can compute portions of a function in parallel; the cascade chain serially connects the intermediate values. The cascade chain can use a logical `AND` or logical `OR` (via De Morgan's inversion) to connect the outputs of adjacent LEs. Each additional LE provides four more inputs to the effective width of a function, with a short cascade delay. Cascade chain logic can be created automatically by the Quartus II software Compiler during design processing, or manually by the designer during design entry.

Cascade chains longer than ten LEs are implemented automatically by linking LABs together. For enhanced fitting, a long cascade chain skips alternate LABs in a MegaLAB structure. A cascade chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure. Figure 7 shows how the cascade function can connect adjacent LEs to form functions with a wide fan-in.

Figure 7. APEX 20K Cascade Chain

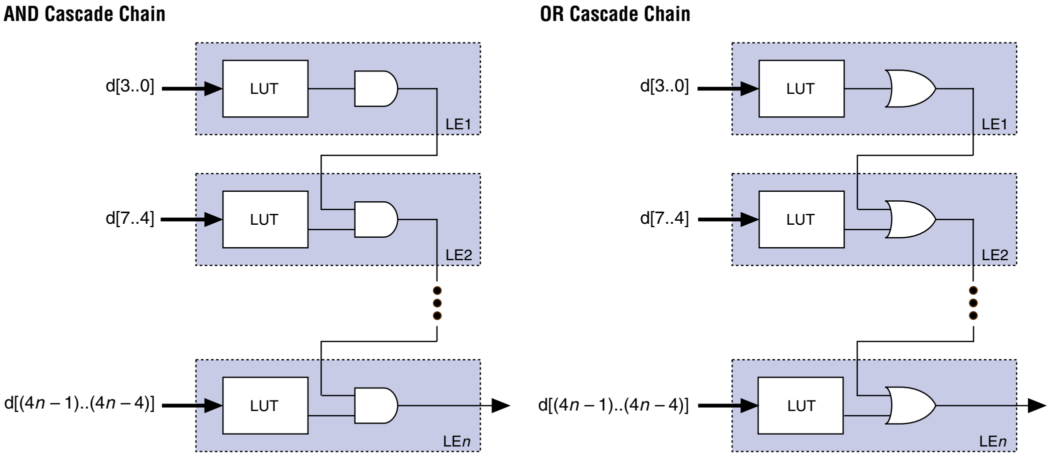
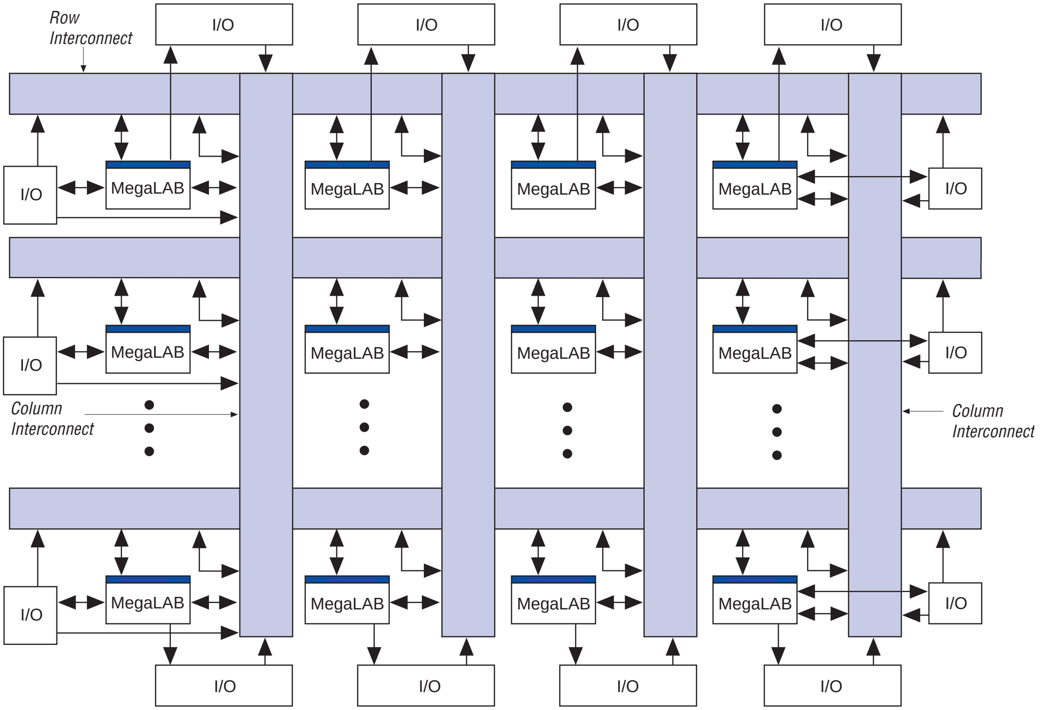


Figure 9. APEX 20K Interconnect Structure

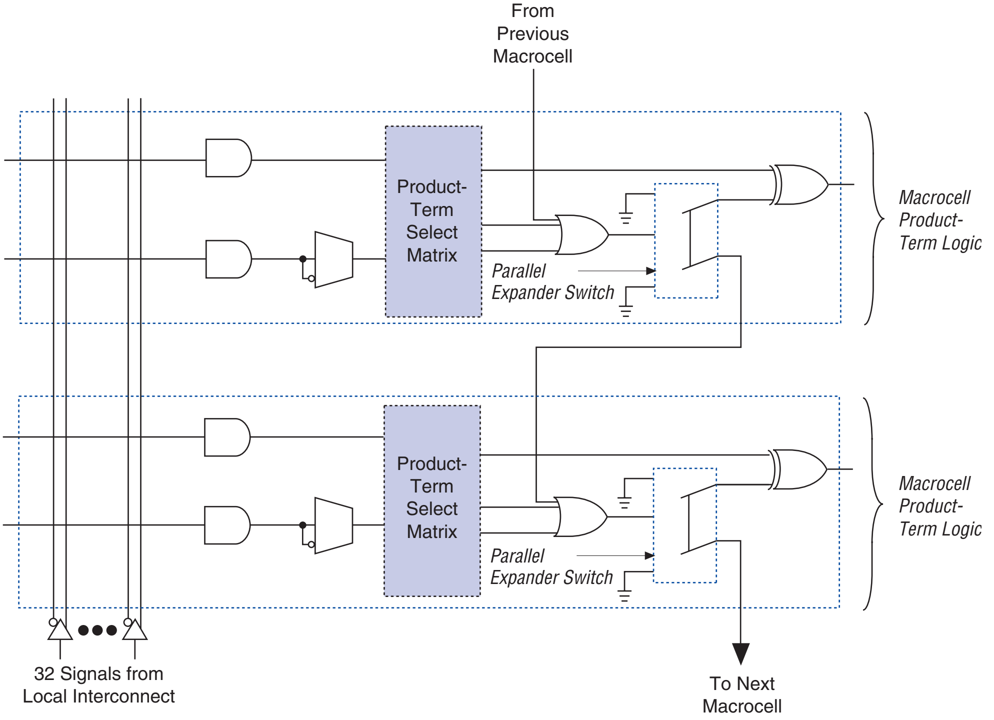


A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack Interconnect uses the local interconnect to drive LEs within MegaLAB structures.

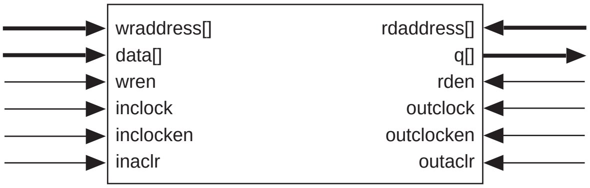
Figure 16. APEX 20K Parallel Expanders



Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

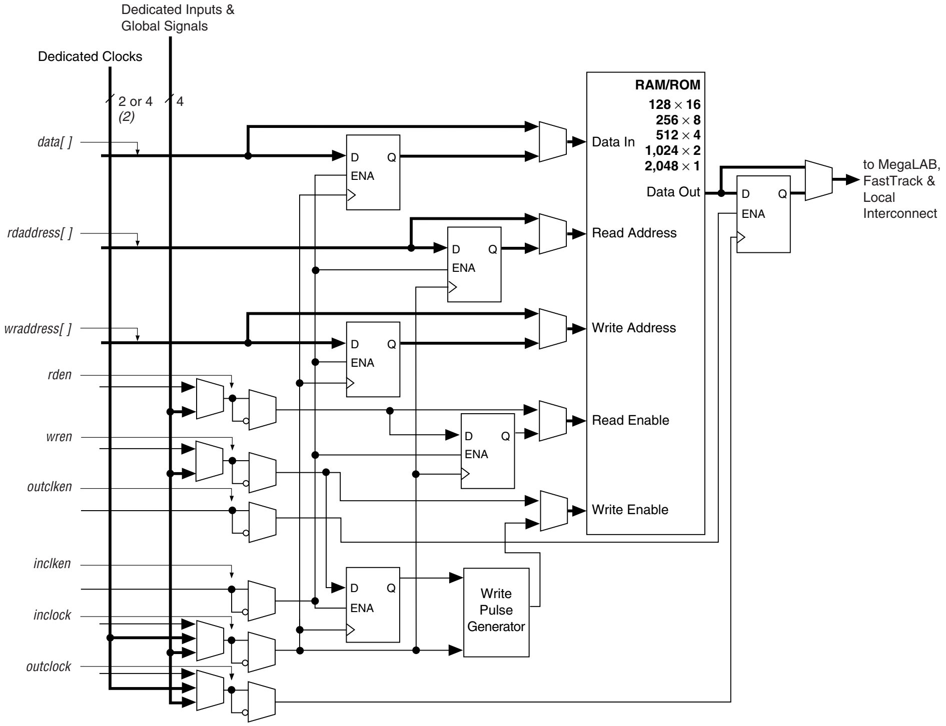
Figure 17. ESB Block Diagram



Input/Output Clock Mode

The input/output clock mode contains two clocks. One clock controls all registers for inputs into the ESB: data input, `WE`, `RE`, read address, and write address. The other clock controls the ESB data output registers. The ESB also supports clock enable and asynchronous clear signals; these signals also control the reading and writing of registers independently. Input/output clock mode is commonly used for applications where the reads and writes occur at the same system frequency, but require different clock enable signals for the input and output registers. Figure 21 shows the ESB in input/output clock mode.

Figure 21. ESB in Input/Output Clock Mode *Note (1)*



Notes to Figure 21:

(1) All registers can be cleared asynchronously by ESB local interconnect signals, global signals, or the chip-wide reset.

(2) APEX 20KE devices have four dedicated clocks.

Single-Port Mode

The APEX 20K ESB also supports a single-port mode, which is used when simultaneous reads and writes are not required. See Figure 22.

Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

Programmable Speed/Power Control

APEX 20K ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB’s power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit™ option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20K device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

I/O Structure

The APEX 20K IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times, or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. For fast bidirectional I/O timing, LE registers using local routing can improve setup times and OE timing. The Quartus II software Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Because the APEX 20K IOE offers one output enable per pin, the Quartus II software Compiler can emulate open-drain operation efficiently.

The APEX 20K IOE includes programmable delays that can be activated to ensure zero hold times, minimum clock-to-output times, input IOE register-to-core register transfers, or core-to-output IOE register transfers. A path in which a pin directly drives a register may require the delay to ensure zero hold time, whereas a path in which a pin drives a register through combinatorial logic may not require the delay.

Under hot socketing conditions, APEX 20KE devices will not sustain any damage, but the I/O pins will drive out.

MultiVolt I/O Interface

The APEX device architecture supports the MultiVolt I/O interface feature, which allows APEX devices in all packages to interface with systems of different supply voltages. The devices have one set of `VCC` pins for internal operation and input buffers (`VCCINT`), and another set for I/O output drivers (`VCCIO`).

The APEX 20K `VCCINT` pins must always be connected to a 2.5 V power supply. With a 2.5-V V_{CCINT} level, input pins are 2.5-V, 3.3-V, and 5.0-V tolerant. The `VCCIO` pins can be connected to either a 2.5-V or 3.3-V power supply, depending on the output requirements. When `VCCIO` pins are connected to a 2.5-V power supply, the output levels are compatible with 2.5-V systems. When the `VCCIO` pins are connected to a 3.3-V power supply, the output high is 3.3 V and is compatible with 3.3-V or 5.0-V systems.

Table 12 summarizes 5.0-V tolerant APEX 20K MultiVolt I/O support.

Table 12. 5.0-V Tolerant APEX 20K MultiVolt I/O Support

V_{CCIO} (V)	Input Signals (V)			Output Signals (V)		
	2.5	3.3	5.0	2.5	3.3	5.0
2.5	✓	✓(1)	✓(1)	✓		
3.3	✓	✓	✓(1)	✓(2)	✓	✓

Notes to Table 12:

(1) The PCI clamping diode must be disabled to drive an input with voltages higher than V_{CCIO}.

(2) When V_{CCIO} = 3.3 V, an APEX 20K device can drive a 2.5-V device with 3.3-V tolerant inputs.

Open-drain output pins on 5.0-V tolerant APEX 20K devices (with a pull-up resistor to the 5.0-V supply) can drive 5.0-V CMOS input pins that require a V_{IH} of 3.5 V. When the pin is inactive, the trace will be pulled up to 5.0 V by the resistor. The open-drain pin will only drive low or tri-state; it will never drive high. The rise time is dependent on the value of the pull-up resistor and load impedance. The I_{OL} current specification should be considered when selecting a pull-up resistor.

Table 21. 32-Bit APEX 20K Device IDCODE

Device	IDCODE (32 Bits) *(1)*			
	Version (4 Bits)	Part Number (16 Bits)	Manufacturer Identity (11 Bits)	1 (1 Bit) *(2)*
EP20K30E	`0000`	`1000 0000 0011 0000`	`000 0110 1110`	1
EP20K60E	`0000`	`1000 0000 0110 0000`	`000 0110 1110`	1
EP20K100	`0000`	`0000 0100 0001 0110`	`000 0110 1110`	1
EP20K100E	`0000`	`1000 0001 0000 0000`	`000 0110 1110`	1
EP20K160E	`0000`	`1000 0001 0110 0000`	`000 0110 1110`	1
EP20K200	`0000`	`0000 1000 0011 0010`	`000 0110 1110`	1
EP20K200E	`0000`	`1000 0010 0000 0000`	`000 0110 1110`	1
EP20K300E	`0000`	`1000 0011 0000 0000`	`000 0110 1110`	1
EP20K400	`0000`	`0001 0110 0110 0100`	`000 0110 1110`	1
EP20K400E	`0000`	`1000 0100 0000 0000`	`000 0110 1110`	1
EP20K600E	`0000`	`1000 0110 0000 0000`	`000 0110 1110`	1
EP20K1000E	`0000`	`1001 0000 0000 0000`	`000 0110 1110`	1

Notes to Table 21:

(1) The most significant bit (MSB) is on the left.

(2) The IDCODE's least significant bit (LSB) is always 1.

Figure 31 shows the timing requirements for the JTAG signals.

Figure 31. APEX 20K JTAG Waveforms

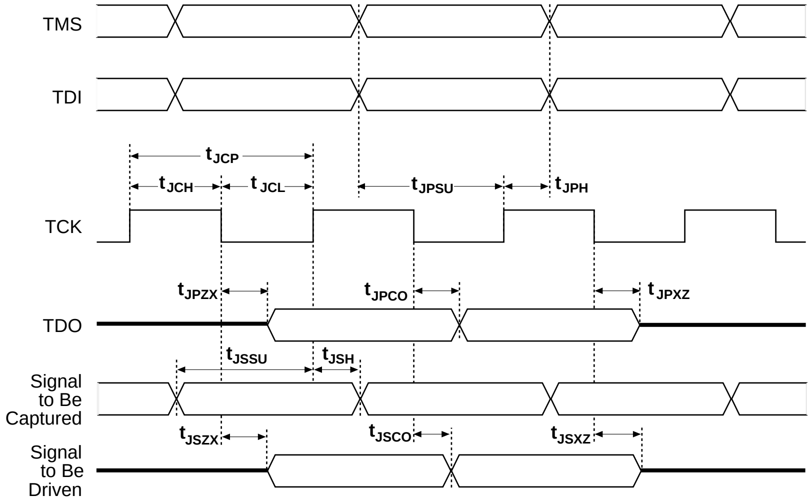


Table 22 shows the JTAG timing parameters and values for APEX 20K devices.

Table 22. APEX 20K JTAG Timing Parameters & Values

Symbol	Parameter	Min	Max	Unit
t_{JCP}	`TCK` clock period	100		ns
t_{JCH}	`TCK` clock high time	50		ns
t_{JCL}	`TCK` clock low time	50		ns
t_{JPSU}	JTAG port setup time	20		ns
t_{JPH}	JTAG port hold time	45		ns
t_{JPCO}	JTAG port clock to output		25	ns
t_{JPZX}	JTAG port high impedance to valid output		25	ns
t_{JPXZ}	JTAG port valid output to high impedance		25	ns
t_{JSSU}	Capture register setup time	20		ns
t_{JSH}	Capture register hold time	45		ns
t_{JSCO}	Update register clock to output		35	ns
t_{JSZX}	Update register high impedance to valid output		35	ns
t_{JSXZ}	Update register valid output to high impedance		35	ns

For more information, see the following documents:

- *Application Note 39 (IEEE Std. 1149.1 (JTAG) Boundary-Scan Testing in Altera Devices)*
- *Jam Programming & Test Language Specification*

Generic Testing

Each APEX 20K device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for APEX 20K devices are made under conditions equivalent to those shown in Figure 32. Multiple test patterns can be used to configure devices during all stages of the production flow.

Table 25. APEX 20K 5.0-V Tolerant Device DC Operating Conditions (Part 2 of 2) *Notes (2), (7), (8)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{OL}	3.3-V low-level TTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(11)*			0.45	V
	3.3-V low-level CMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(11)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*			$0.1 \times V_{CCIO}$	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(11)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(11)*			0.7	V
I_I	Input pin leakage current	V_I = 5.75 to –0.5 V	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 5.75 to –0.5 V	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade *(12)*		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades *(12)*		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(13)*	20		50	W
		V_{CCIO} = 2.375 V *(13)*	30		80	W

Table 29. APEX 20KE Device DC Operating Conditions *Notes (7), (8), (9)*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IH}	High-level LVTTL, CMOS, or 3.3-V PCI input voltage		1.7, 0.5 × V_{CCIO} *(10)*		4.1	V
V_{IL}	Low-level LVTTL, CMOS, or 3.3-V PCI input voltage		–0.5		0.8, 0.3 × V_{CCIO} *(10)*	V
V_{OH}	3.3-V high-level LVTTL output voltage	I_{OH} = –12 mA DC, V_{CCIO} = 3.00 V *(11)*	2.4			V
	3.3-V high-level LVCMOS output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 3.00 V *(11)*	V_{CCIO} – 0.2			V
	3.3-V high-level PCI output voltage	I_{OH} = –0.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(11)*	0.9 × V_{CCIO}			V
	2.5-V high-level output voltage	I_{OH} = –0.1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.1			V
		I_{OH} = –1 mA DC, V_{CCIO} = 2.30 V *(11)*	2.0			V
		I_{OH} = –2 mA DC, V_{CCIO} = 2.30 V *(11)*	1.7			V
V_{OL}	3.3-V low-level LVTTL output voltage	I_{OL} = 12 mA DC, V_{CCIO} = 3.00 V *(12)*			0.4	V
	3.3-V low-level LVCMOS output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 3.00 V *(12)*			0.2	V
	3.3-V low-level PCI output voltage	I_{OL} = 1.5 mA DC, V_{CCIO} = 3.00 to 3.60 V *(12)*			0.1 × V_{CCIO}	V
	2.5-V low-level output voltage	I_{OL} = 0.1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.2	V
		I_{OL} = 1 mA DC, V_{CCIO} = 2.30 V *(12)*			0.4	V
		I_{OL} = 2 mA DC, V_{CCIO} = 2.30 V *(12)*			0.7	V
I_I	Input pin leakage current	V_I = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{OZ}	Tri-stated I/O pin leakage current	V_O = 4.1 to –0.5 V *(13)*	–10		10	µA
I_{CC0}	V_{CC} supply current (standby) (All ESBs in power-down mode)	V_I = ground, no load, no toggling inputs, -1 speed grade		10		mA
		V_I = ground, no load, no toggling inputs, -2, -3 speed grades		5		mA
R_{CONF}	Value of I/O pin pull-up resistor before and during configuration	V_{CCIO} = 3.0 V *(14)*	20		50	kΩ
		V_{CCIO} = 2.375 V *(14)*	30		80	kΩ
		V_{CCIO} = 1.71 V *(14)*	60		150	kΩ

All specifications are always representative of worst-case supply voltage and junction temperature conditions. All output-pin-timing specifications are reported for maximum driver strength.

Figure 36 shows the f_{MAX} timing model for APEX 20K devices.

Figure 36. APEX 20K f_{MAX} Timing Model

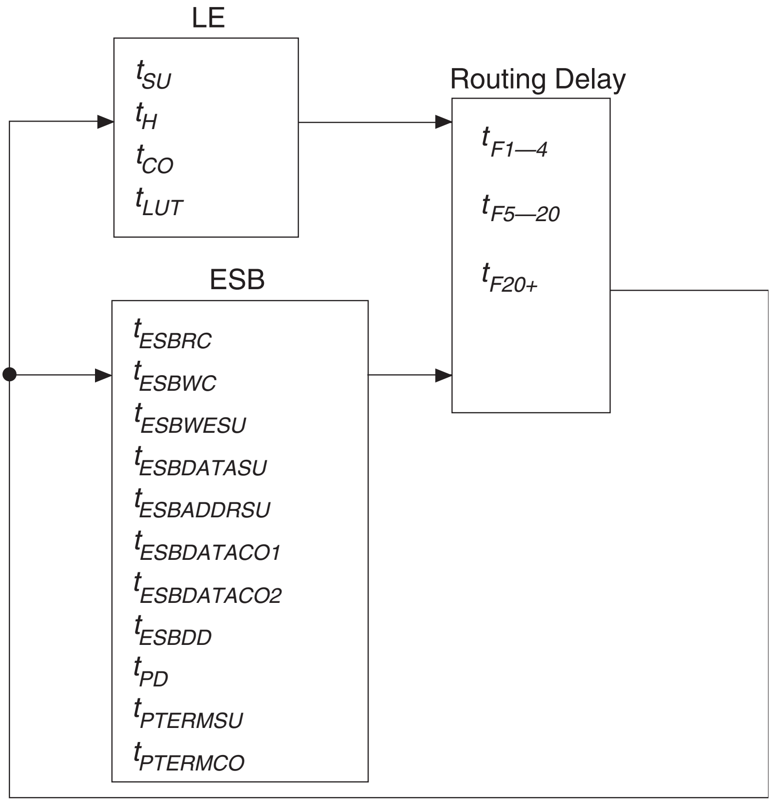


Figure 37 shows the f_{MAX} timing model for APEX 20KE devices. These parameters can be used to estimate f_{MAX} for multiple levels of logic. Quartus II software timing analysis should be used for more accurate timing information.

Figure 39. ESB Synchronous Timing Waveforms

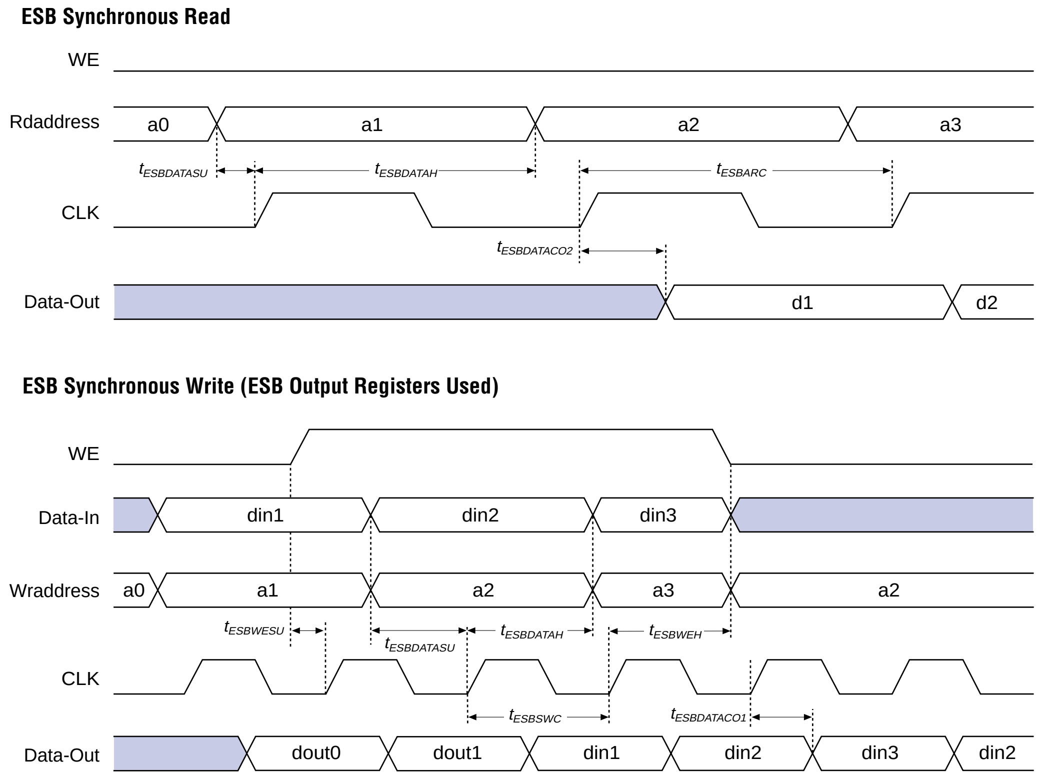


Figure 40 shows the timing model for bidirectional I/O pin timing.

Table 41. EP20K200 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.5		0.6		0.8		ns
t_{H}	0.7		0.8		1.0		ns
t_{CO}		0.3		0.4		0.5	ns
t_{LUT}		0.8		1.0		1.3	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.6		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.0		3.6	ns
$t_{PTERMSU}$	2.3		2.7		3.2		ns
$t_{PTERMCO}$		1.5		1.8		2.1	ns
t_{F1-4}		0.5		0.6		0.7	ns
t_{F5-20}		1.6		1.7		1.8	ns
t_{F20+}		2.2		2.2		2.3	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.3		0.4		0.4		ns
t_{PREP}	0.4		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.6		1.9		2.2		ns
t_{ESBRP}	1.0		1.3		1.4		ns

Table 42. EP20K400 f_{MAX} Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Units
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.1		0.3		0.6		ns
t_{H}	0.5		0.8		0.9		ns
t_{CO}		0.1		0.4		0.6	ns
t_{LUT}		1.0		1.2		1.4	ns
t_{ESBRC}		1.7		2.1		2.4	ns
t_{ESBWC}		5.7		6.9		8.1	ns
$t_{ESBWESU}$	3.3		3.9		4.6		ns
$t_{ESBDATASU}$	2.2		2.7		3.1		ns
$t_{ESBDATAH}$	0.6		0.8		0.9		ns
$t_{ESBADDRSU}$	2.4		2.9		3.3		ns
$t_{ESBDATACO1}$		1.3		1.6		1.8	ns
$t_{ESBDATACO2}$		2.5		3.1		3.6	ns
t_{ESBDD}		2.5		3.3		3.6	ns
t_{PD}		2.5		3.1		3.6	ns
$t_{PTERMSU}$	1.7		2.1		2.4		ns
$t_{PTERMCO}$		1.0		1.2		1.4	ns
t_{F1-4}		0.4		0.5		0.6	ns
t_{F5-20}		2.6		2.8		2.9	ns
t_{F20+}		3.7		3.8		3.9	ns
t_{CH}	2.0		2.5		3.0		ns
t_{CL}	2.0		2.5		3.0		ns
t_{CLRP}	0.5		0.6		0.8		ns
t_{PREP}	0.5		0.5		0.5		ns
t_{ESBCH}	2.0		2.5		3.0		ns
t_{ESBCL}	2.0		2.5		3.0		ns
t_{ESBWP}	1.5		1.9		2.2		ns
t_{ESBRP}	1.0		1.2		1.4		ns

Tables 43 through 48 show the I/O external and external bidirectional timing parameter values for EP20K100, EP20K200, and EP20K400 APEX 20K devices.

Table 52. EP20K30E Minimum Pulse Width Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	0.55		0.78		1.15		ns
t_{CL}	0.55		0.78		1.15		ns
t_{CLRP}	0.22		0.31		0.46		ns
t_{PREP}	0.22		0.31		0.46		ns
t_{ESBCH}	0.55		0.78		1.15		ns
t_{ESBCL}	0.55		0.78		1.15		ns
t_{ESBWP}	1.43		2.01		2.97		ns
t_{ESBRP}	1.15		1.62		2.39		ns

Table 53. EP20K30E External Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.02		2.13		2.24		ns
t_{INH}	0.00		0.00		0.00		ns
t_{OUTCO}	2.00	4.88	2.00	5.36	2.00	5.88	ns
$t_{INSUPLL}$	2.11		2.23		-		ns
t_{INHPLL}	0.00		0.00		-		ns
$t_{OUTCOPLL}$	0.50	2.60	0.50	2.88	-	-	ns

Table 54. EP20K30E External Bidirectional Timing Parameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	1.85		1.77		1.54		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	4.88	2.00	5.36	2.00	5.88	ns
$t_{XZBIDIR}$		7.48		8.46		9.83	ns
$t_{ZXBIDIR}$		7.48		8.46		9.83	ns
$t_{INSUBIDIRPLL}$	4.12		4.24		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.60	0.50	2.88	-	-	ns
$t_{XZBIDIRPLL}$		5.21		5.99		-	ns
$t_{ZXBIDIRPLL}$		5.21		5.99		-	ns

Tables 55 through 60 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K60E APEX 20KE devices.

Table 55. EP20K60E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.17		0.15		0.16		ns
t_{H}	0.32		0.33		0.39		ns
t_{CO}		0.29		0.40		0.60	ns
t_{LUT}		0.77		1.07		1.59	ns

Tables 67 through 72 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K160E APEX 20KE devices.

Table 67. EP20K160E f_{MAX} LE Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.22		0.24		0.26		ns
t_{H}	0.22		0.24		0.26		ns
t_{CO}		0.25		0.31		0.35	ns
t_{LUT}		0.69		0.88		1.12	ns

Table 74. EP20K200E f_{MAX} ESB Timing Microparameters

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.68		2.06		2.24	ns
t_{ESBSRC}		2.27		2.77		3.18	ns
t_{ESBAWC}		3.10		3.86		4.50	ns
t_{ESBSWC}		2.90		3.67		4.21	ns
$t_{ESBWASU}$	0.55		0.67		0.74		ns
t_{ESBWAH}	0.36		0.46		0.48		ns
$t_{ESBWDSU}$	0.69		0.83		0.95		ns
t_{ESBWDH}	0.36		0.46		0.48		ns
$t_{ESBRASU}$	1.61		1.90		2.09		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.42		1.71		2.01		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.06		-0.07		0.05		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	0.11		0.13		0.31		ns
$t_{ESBRADDRSU}$	0.18		0.23		0.39		ns
$t_{ESBDATACO1}$		1.09		1.35		1.51	ns
$t_{ESBDATACO2}$		2.19		2.75		3.22	ns
t_{ESBDD}		2.75		3.41		4.03	ns
t_{PD}		1.58		1.97		2.33	ns
$t_{PTERMSU}$	1.00		1.22		1.51		ns
$t_{PTERMCO}$		1.10		1.37		1.09	ns

Table 75. EP20K200E f_{MAX} Routing Delays

Symbol	-1		-2		-3		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}		0.25		0.27		0.29	ns
t_{F5-20}		1.02		1.20		1.41	ns
t_{F20+}		1.99		2.23		2.53	ns

Table 86. EP20K400E f_{MAX} ESB Timing Microparameters							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{ESBARC}		1.67		1.91		1.99	ns
t_{ESBSRC}		2.30		2.66		2.93	ns
t_{ESBAWC}		3.09		3.58		3.99	ns
t_{ESBSWC}		3.01		3.65		4.05	ns
$t_{ESBWASU}$	0.54		0.63		0.65		ns
t_{ESBWAH}	0.36		0.43		0.42		ns
$t_{ESBWDSU}$	0.69		0.77		0.84		ns
t_{ESBWDH}	0.36		0.43		0.42		ns
$t_{ESBRASU}$	1.61		1.77		1.86		ns
t_{ESBRAH}	0.00		0.00		0.01		ns
$t_{ESBWESU}$	1.35		1.47		1.61		ns
t_{ESBWEH}	0.00		0.00		0.00		ns
$t_{ESBDATASU}$	-0.18		-0.30		-0.27		ns
$t_{ESBDATAH}$	0.13		0.13		0.13		ns
$t_{ESBWADDRSU}$	-0.02		-0.11		-0.03		ns
$t_{ESBRADDRSU}$	0.06		-0.01		-0.05		ns
$t_{ESBDATACO1}$		1.16		1.40		1.54	ns
$t_{ESBDATACO2}$		2.18		2.55		2.85	ns
t_{ESBDD}		2.73		3.17		3.58	ns
t_{PD}		1.57		1.83		2.07	ns
$t_{PTERMSU}$	0.92		0.99		1.18		ns
$t_{PTERMCO}$		1.18		1.43		1.17	ns

Table 90. EP20K400E External Bidirectional Timing Parameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$	2.93		3.23		3.44		ns
$t_{INHBIDIR}$	0.00		0.00		0.00		ns
$t_{OUTCOBIDIR}$	2.00	5.25	2.00	5.79	2.00	6.32	ns
$t_{XZBIDIR}$		5.95		6.77		7.12	ns
$t_{ZXBIDIR}$		5.95		6.77		7.12	ns
$t_{INSUBIDIRPLL}$	4.31		4.76		-		ns
$t_{INHBIDIRPLL}$	0.00		0.00		-		ns
$t_{OUTCOBIDIRPLL}$	0.50	2.25	0.50	2.45	-	-	ns
$t_{XZBIDIRPLL}$		2.94		3.43		-	ns
$t_{ZXBIDIRPLL}$		2.94		3.43		-	ns

Tables 91 through 96 describe f_{MAX} LE Timing Microparameters, f_{MAX} ESB Timing Microparameters, f_{MAX} Routing Delays, Minimum Pulse Width Timing Parameters, External Timing Parameters, and External Bidirectional Timing Parameters for EP20K600E APEX 20KE devices.

Table 91. EP20K600E f_{MAX} LE Timing Microparameters

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.16		0.16		0.17		ns
t_H	0.29		0.33		0.37		ns
t_{CO}		0.65		0.38		0.49	ns
t_{LUT}		0.70		1.00		1.30	ns